

F1310NL-VB Datasheet

N-Channel 100-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
100	0.0085 at $V_{GS} = 10$ V	100
	0.010 at $V_{GS} = 6$ V	85

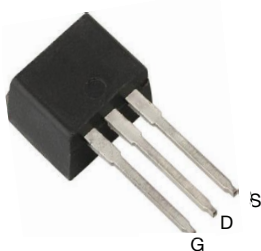
FEATURES

- Trench Power MOSFET
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC

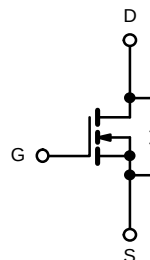


RoHS
COMPLIANT

TO-262



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	100	A
	T _C = 125 °C		75 ^a	
Pulsed Drain Current		I _{DM}	300	
Avalanche Current	L = 0.1 mH	I _{AS}	75	
Single Pulse Avalanche Energy ^b		E _{AS}	280	mJ
Maximum Power Dissipation ^b	T _C = 25 °C (TO-220AB and TO-263)	P _D	250 ^c	W
	T _A = 25 °C (TO-263) ^d		3.75	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
		62.5	
Junction-to-Case	R_{thJC}	0.6	

Notes:

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

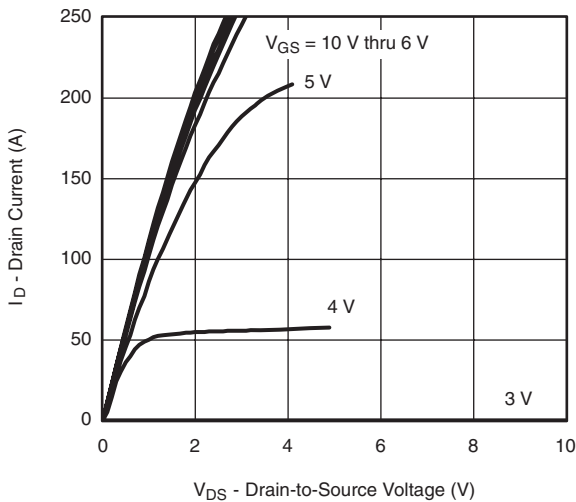
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1		3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	120			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$		0.0085		Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 20\text{ A}$		0.010		
		$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		0.017		
		$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$		0.022		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 30\text{ A}$	25			S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		6550		pF
Output Capacitance	C_{oss}			665		
Reverse Transfer Capacitance	C_{rss}			265		
Total Gate Charge ^c	Q_g	$V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 85\text{ A}$		105	160	nC
Gate-Source Charge ^c	Q_{gs}			17		
Gate-Drain Charge ^c	Q_{gd}			23		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 50\text{ V}$, $R_L = 0.6\text{ }\Omega$ $I_D \cong 85\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 2.5\text{ }\Omega$		12	25	ns
Rise Time ^c	t_r			90	135	
Turn-Off DelayTime ^c	$t_{d(off)}$			55	85	
Fall Time ^c	t_f			130	195	
Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}$ ^b						
Continuous Current	I_S				85	A
Pulsed Current	I_{SM}				240	
Forward Voltage ^a	V_{SD}	$I_F = 85\text{ A}$, $V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 50\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$		85	140	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			4.5	7	A
Reverse Recovery Charge	Q_{rr}			0.17	0.35	μC

Notes:

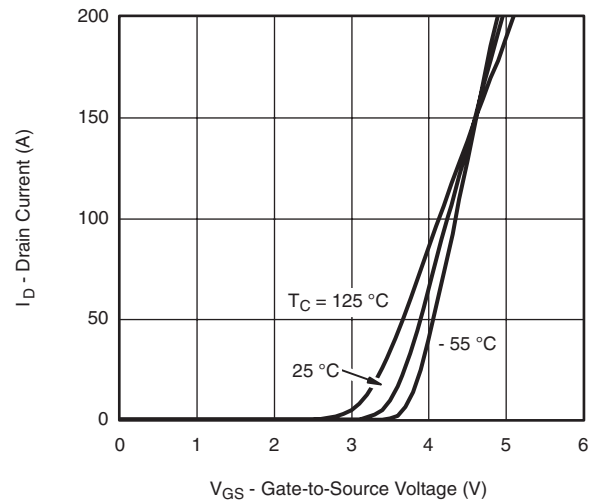
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

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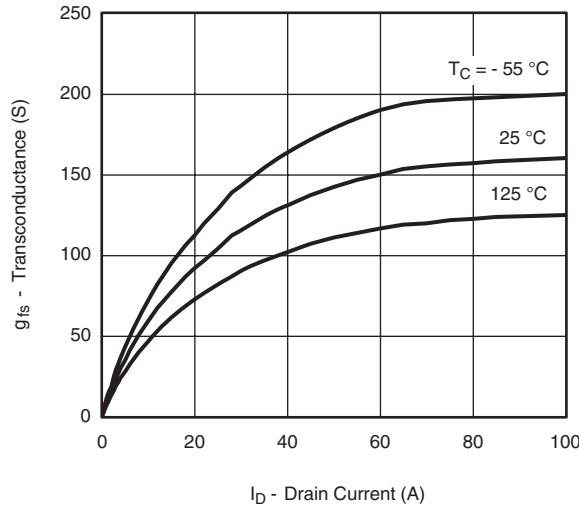
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted



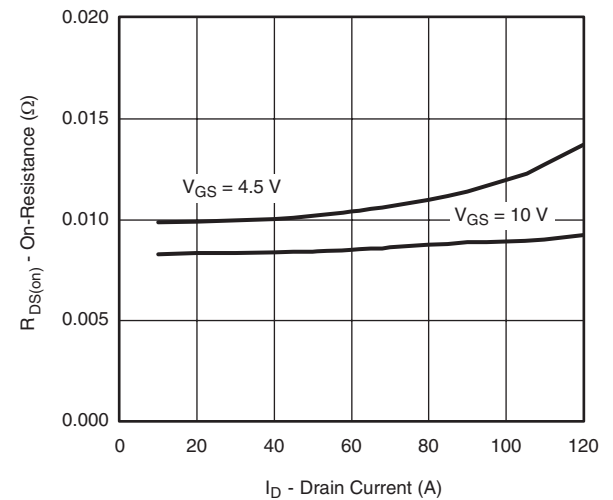
Output Characteristics



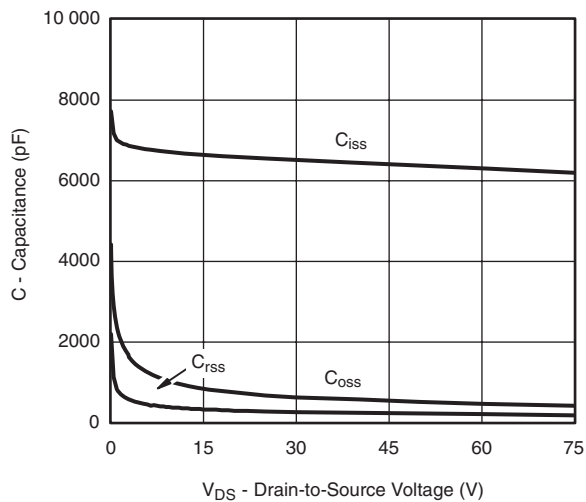
Transfer Characteristics



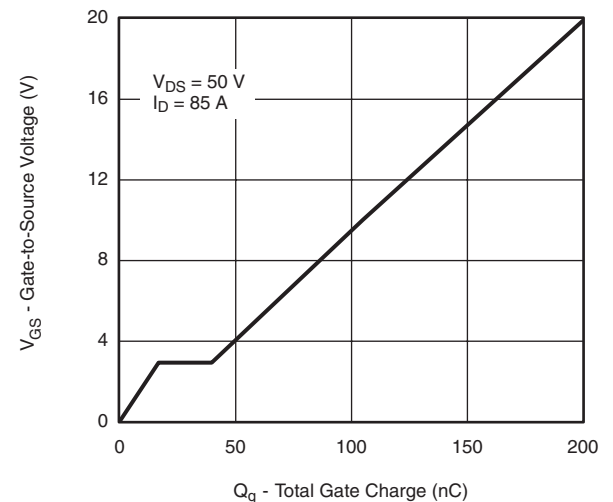
Transconductance



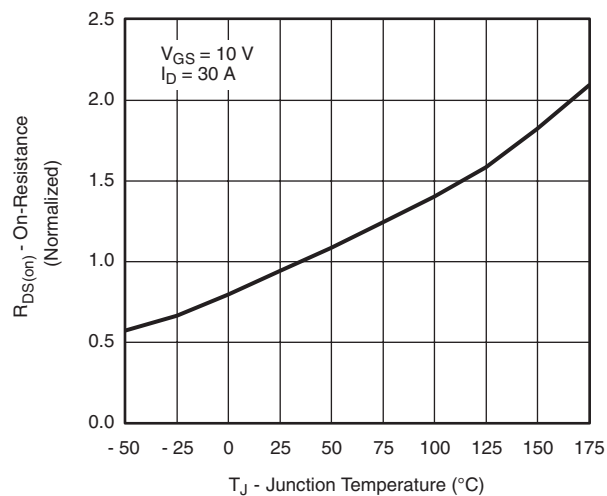
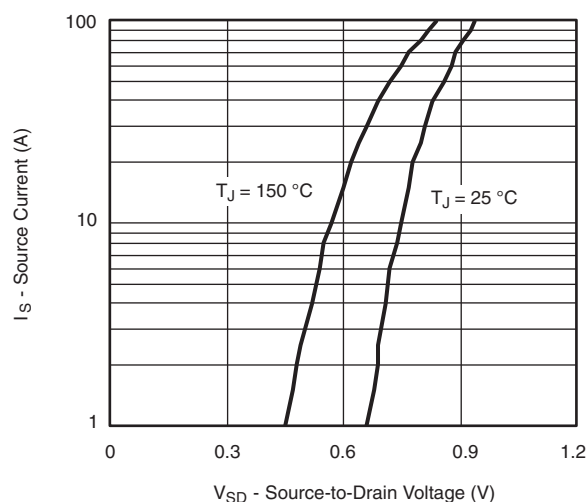
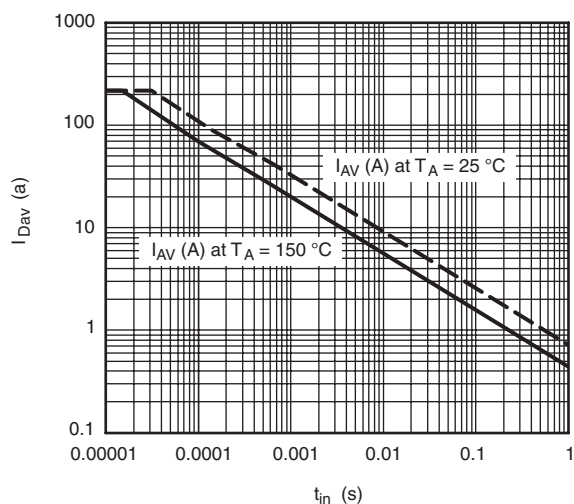
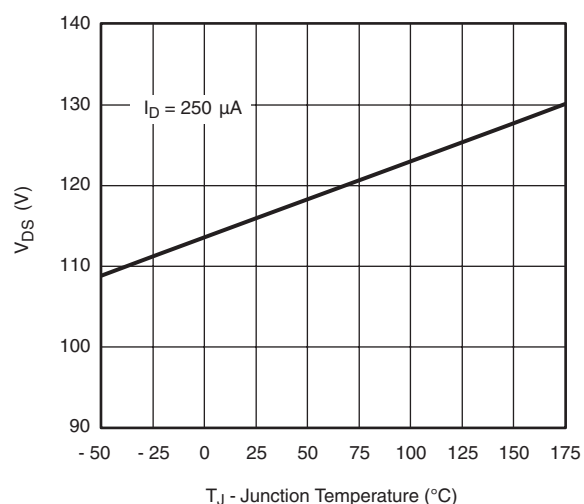
On-Resistance vs. Drain Current



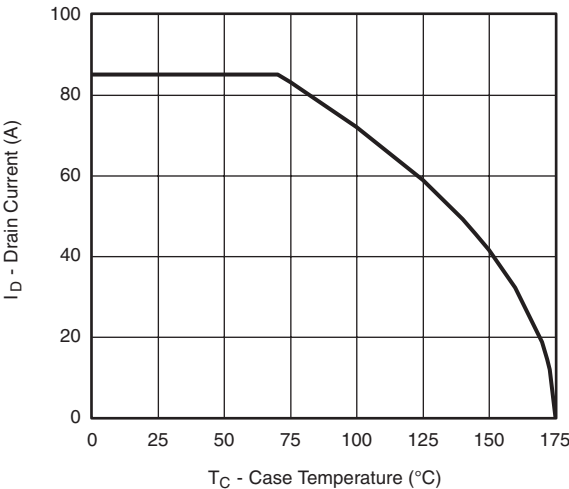
Capacitance



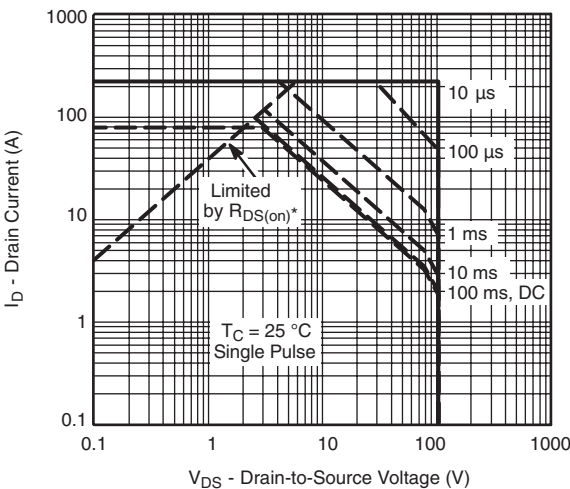
Gate Charge

TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

Avalanche Current vs. Time

 T_J - Drain-Source Breakdown vs. Junction-Temperature

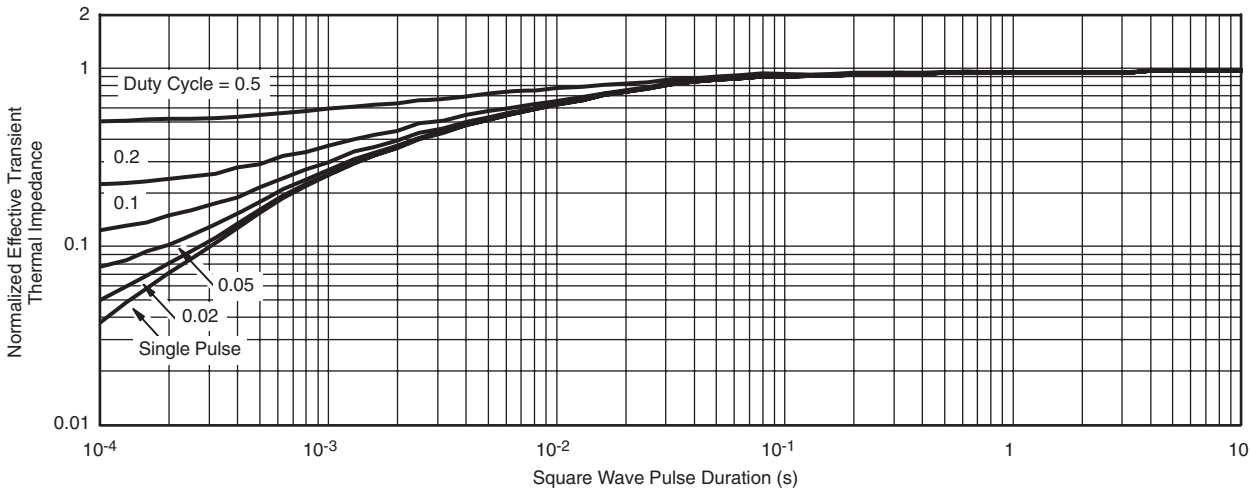
THERMAL RATINGS



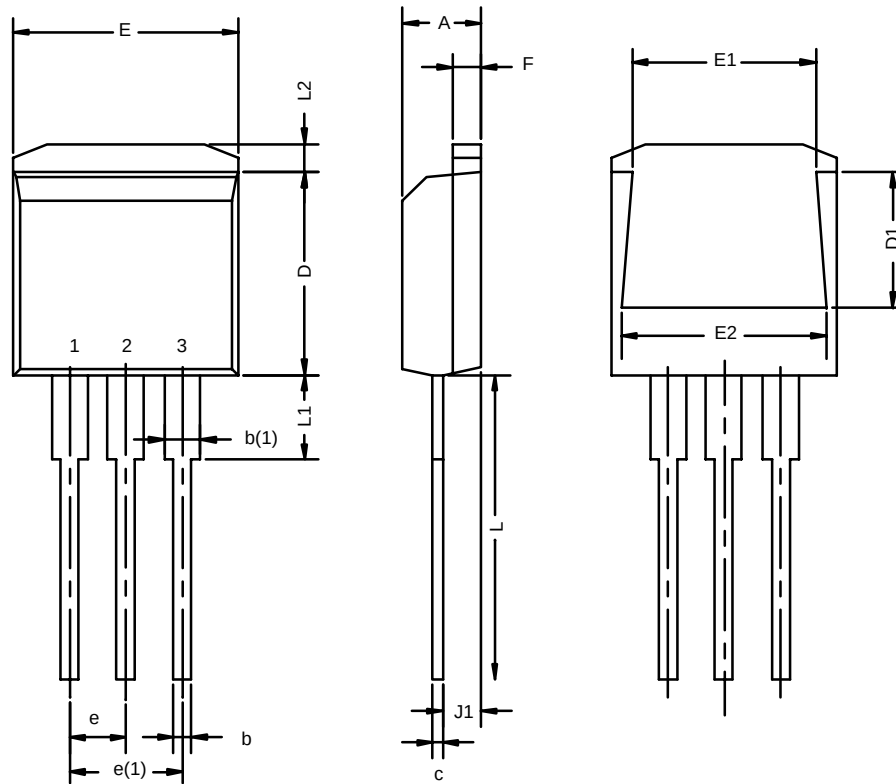
**Maximum Avalanche and Drain Current
vs. Case Temperature**



Safe Operating Area
* $V_{GS} > \text{minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$



Normalized Thermal Transient Impedance, Junction-to-Case

TO-262: 3-LEAD

Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
A	4.32	4.70	0.170	0.185
b	0.64	1.00	0.025	0.039
b(1)	1.14	1.40	0.045	0.055
c	0.36	0.50	0.014	0.020
D	8.64	9.65	0.340	0.380
D1	5.59	6.10	0.220	0.240
e	2.41	2.67	0.095	0.105
e(1)	4.95	5.33	0.195	0.210
E	10.03	10.41	0.395	0.410
E1	7.87	8.64	0.310	0.340
E2	9.02	9.53	0.355	0.375
F	1.14	1.40	0.045	0.055
J1	2.41	2.79	0.095	0.110
L	13.08	14.22	0.515	0.560
L1	-	3.81	-	0.150
L2	1.02	1.40	0.040	0.055
ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855				

*Use millimeters as the primary measurement

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